

N- and P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	40	0.016 at V _{GS} = 10 V	8	56
		0.019 at V _{GS} = 4.5 V	8	
P-Channel	- 40	0.025 at V _{GS} = - 10 V	- 8	6
		0.032 at V _{GS} = - 4.5 V	- 7.5	

FEATURES

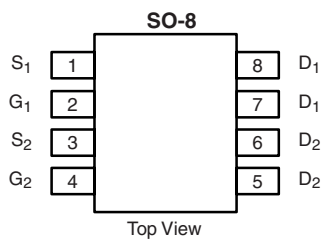
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 % R_g Tested



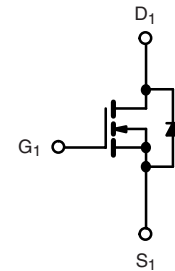
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

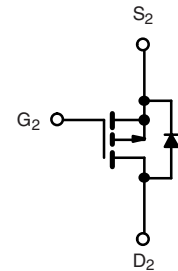
- CCFL Inverter



Ordering Information: Si4563DY-T1-E3 (Lead (Pb)-free)
Si4563DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V _{DS}	40	- 40	V
Gate-Source Voltage		V _{GS}	± 16		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	8	- 8	A
	T _C = 70 °C		8	- 6.5	
	T _A = 25 °C		8 ^{b, c}	- 6.6 ^{b, c}	
	T _A = 70 °C		6.5 ^{b, c}	- 5.2 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	20	- 20	
Source-Drain Current Diode Current	T _C = 25 °C	I _S	2.7	- 2.7	
	T _A = 25 °C		1.6 ^{b, c}	- 1.6 ^{b, c}	
Pulsed Source-Drain Current		I _{SM}	20	- 20	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	25	
Single Pulse Avalanche Energy		E _{AS}	20	31.2	
Maximum Power Dissipation	T _C = 25 °C	P _D	3.25	3.25	W
	T _C = 70 °C		2.10	2.10	
	T _A = 25 °C		2.0 ^{b, c}	2.0 ^{b, c}	
	T _A = 70 °C		1.25 ^{b, c}	1.25 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	45	62.5	45	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	29	38	29	38	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 120 °C/W.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	N-Ch	40			V	
		V _{GS} = 0 V, I _D = - 250 μA	P-Ch	- 40				
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	N-Ch		40		mV/°C	
		I _D = - 250 μA	P-Ch		- 40			
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	N-Ch		- 4.8			
		I _D = - 250 μA	P-Ch		4.0			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.8		2.0	V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.8		- 2.2		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 16 V	N-Ch P-Ch			100 - 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = - 40 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			10		
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 10		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	N-Ch	20			A	
		V _{DS} = - 5 V, V _{GS} = - 10 V	P-Ch	- 20				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A	N-Ch		0.013	0.016	Ω	
		V _{GS} = - 10 V, I _D = - 5 A	P-Ch		0.020	0.025		
		V _{GS} = 4.5 V, I _D = 4 A	N-Ch		0.015	0.019		
		V _{GS} = - 4.5 V, I _D = - 4 A	P-Ch		0.025	0.032		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 5 A	N-Ch		23		S	
		V _{DS} = - 15 V, I _D = - 5 A	P-Ch		18			
Dynamic ^a								
Input Capacitance	C _{iss}	N-Channel V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz P-Channel V _{DS} = - 20 V, V _{GS} = 0 V, f = 1 MHz	N-Ch		2390		pF	
			P-Ch		2120			
Output Capacitance	C _{oss}		N-Ch		270			
			P-Ch		310			
Reverse Transfer Capacitance	C _{rss}	N-Ch		165				
		P-Ch		235				
Total Gate Charge	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 5 A	N-Ch		56	85	nC	
		V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 5 A	P-Ch		52	80		
		N-Channel V _{DS} = 20 V, V _{GS} = 4.5 V I _D = 5 A	N-Ch		26	40		
			P-Ch		25.5	39		
Gate-Source Charge	Q _{gs}	N-Ch		5.5				
		P-Ch		5.1				
Gate-Drain Charge	Q _{gd}	N-Ch		9.7				
		P-Ch		11.7				
Gate Resistance	R _g	f = 1 MHz	N-Ch		2.6	4.0	Ω	
			P-Ch		5.8	9.0		



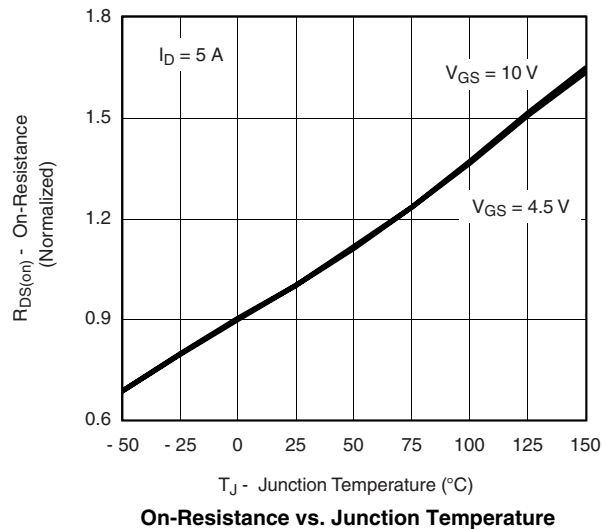
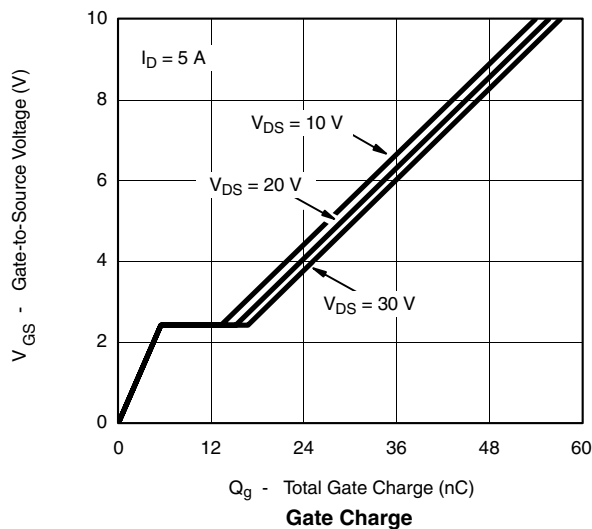
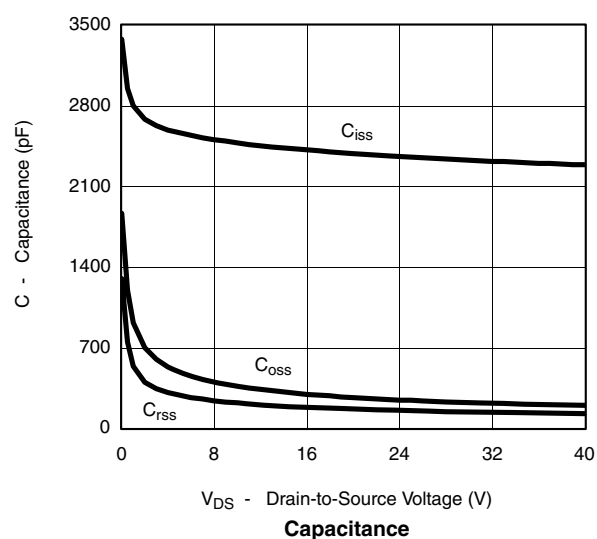
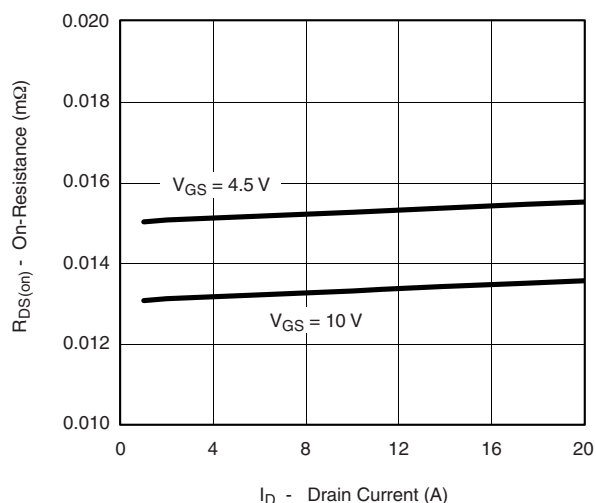
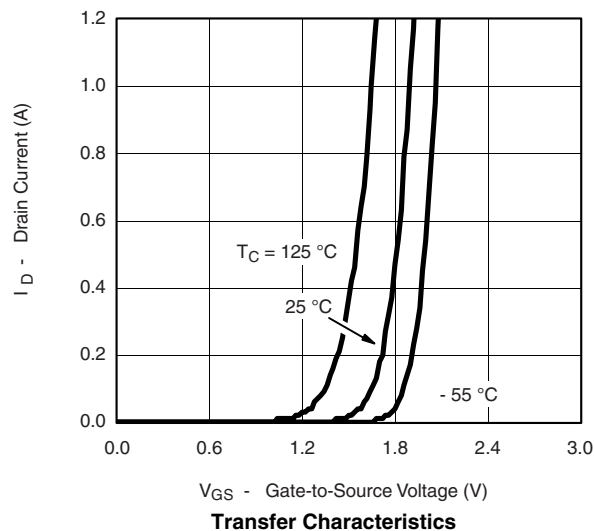
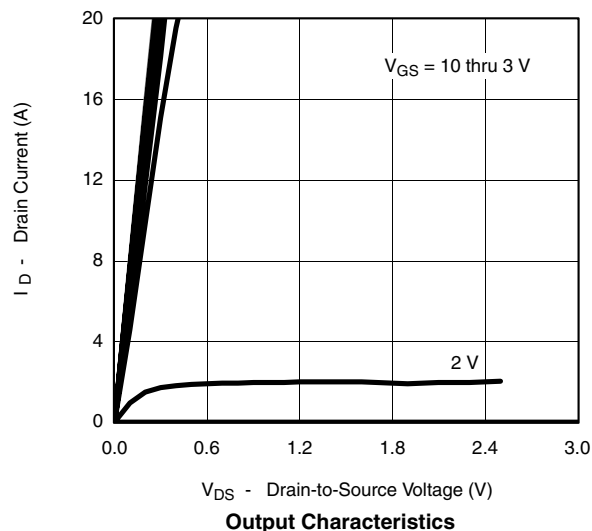
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Dynamic ^a							
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 20 V, R _L = 4 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch		15	23	ns
			P-Ch		13	20	
Rise Time	t _r		N-Ch		20	30	
			P-Ch		16	25	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 20 V, R _L = 4 Ω I _D ≅ - 5 A, V _{GEN} = - 10 V, R _g = 1 Ω	N-Ch		56	85	
			P-Ch		75	115	
Fall Time	t _f		N-Ch		10	15	
			P-Ch		68	105	
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 20 V, R _L = 4 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω	N-Ch		88	135	
			P-Ch		33	50	
Rise Time	t _r		N-Ch		117	180	
			P-Ch		93	140	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 20 V, R _L = 4 Ω I _D ≅ - 5 A, V _{GEN} = - 4.5 V, R _g = 16 Ω	N-Ch		62	95	
			P-Ch		80	120	
Fall Time	t _f		N-Ch		19	30	
			P-Ch		69	105	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	N-Ch			2.7	A
			P-Ch			- 2.7	
Pulse Diode Forward Current ^a	I _{SM}		N-Ch			20	
			P-Ch			- 20	
Body Diode Voltage	V _{SD}	I _S = 1.5 A	N-Ch		0.69	1.2	V
		I _S = - 1.6 A	P-Ch		- 0.72	- 1.2	
Body Diode Reverse Recovery Time	t _{rr}	N-Channel I _F = 2 A, dI/dt = 100 A/μs, T _J = 25 °C	N-Ch		62	95	ns
			P-Ch		49	75	
Body Diode Reverse Recovery Charge	Q _{rr}		N-Ch		62	95	nC
			P-Ch		42	65	
Reverse Recovery Fall Time	t _a	P-Channel I _F = - 2 A, dI/dt = - 100 A/μs, T _J = 25 °C	N-Ch		26		ns
			P-Ch		19		
Reverse Recovery Rise Time	t _b		N-Ch		36		
			P-Ch		30		

Notes:

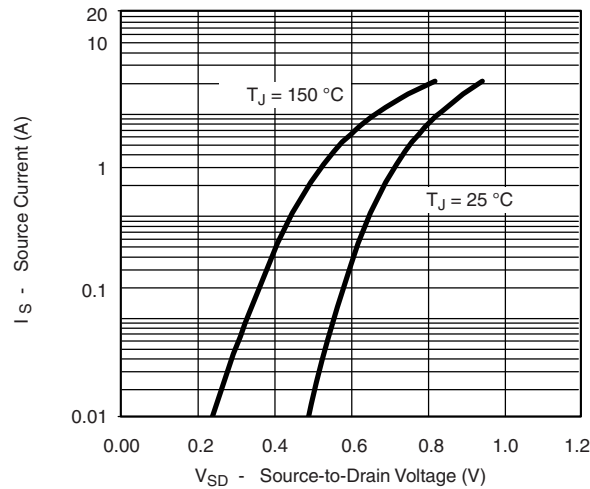
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\text{ }\%$.

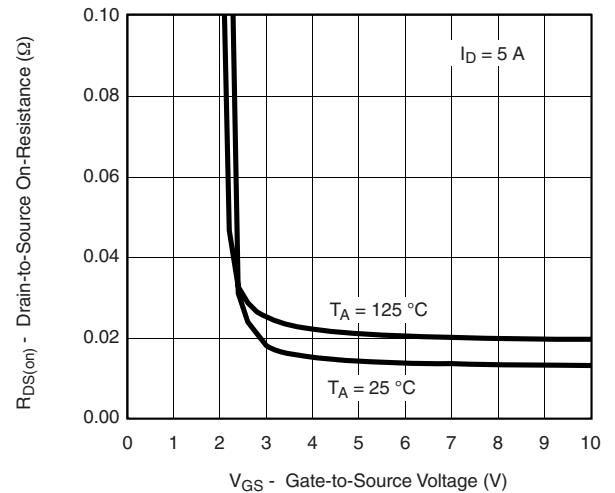
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

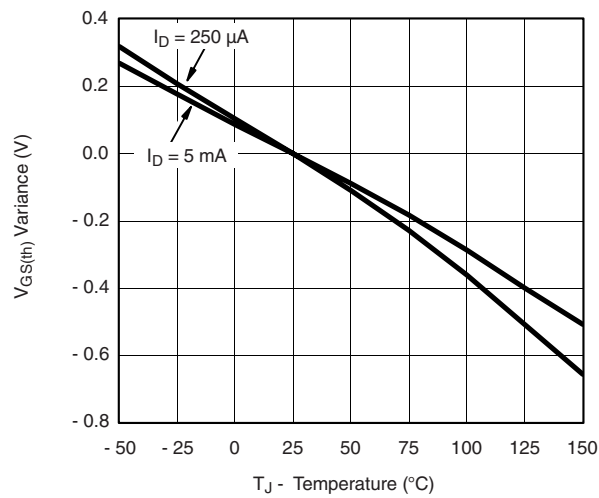
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



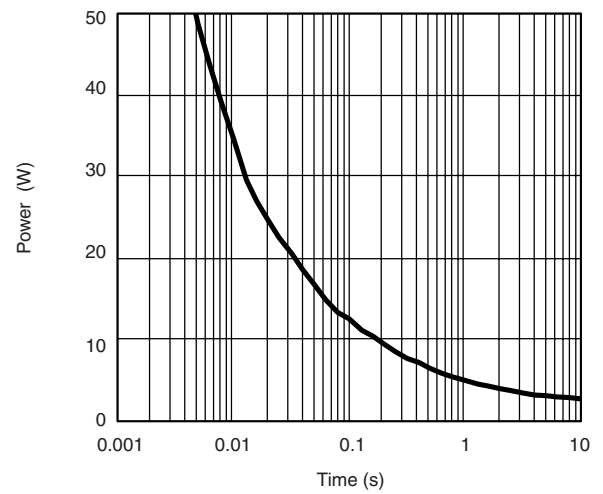
Source-Drain Diode Forward Voltage



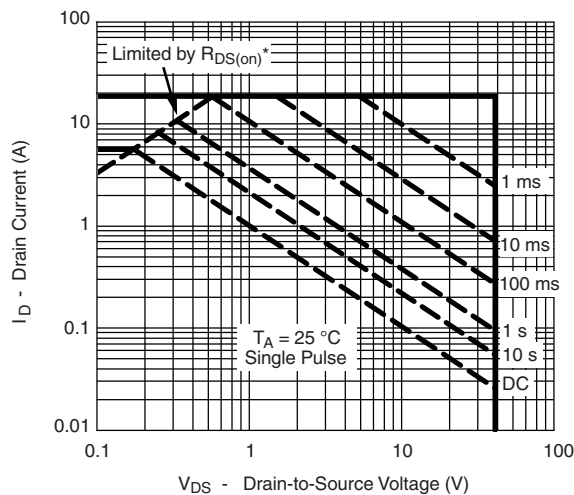
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

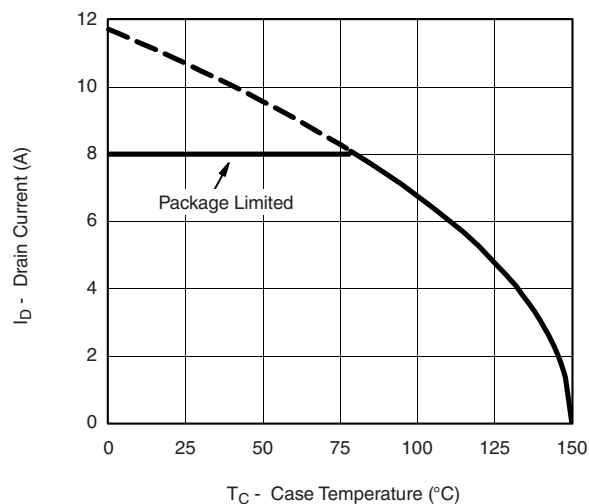
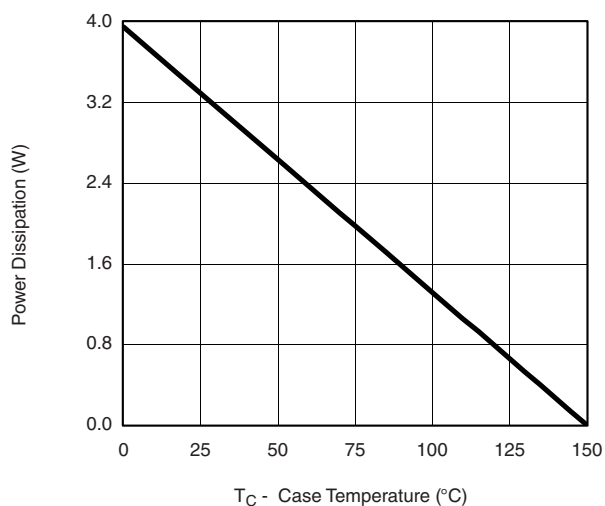
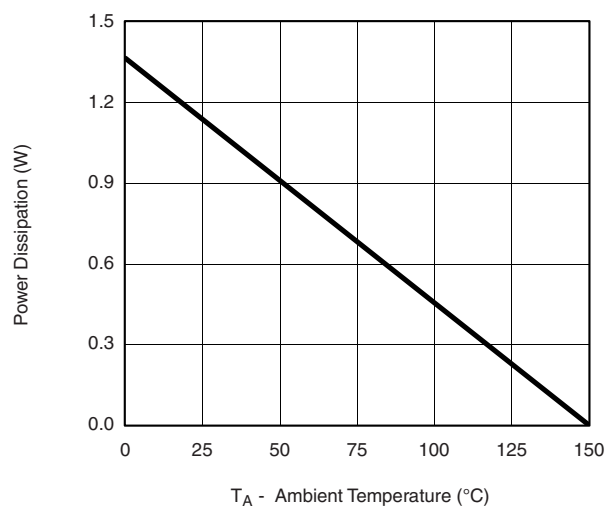


Single Pulse Power, Junction-to-Ambient



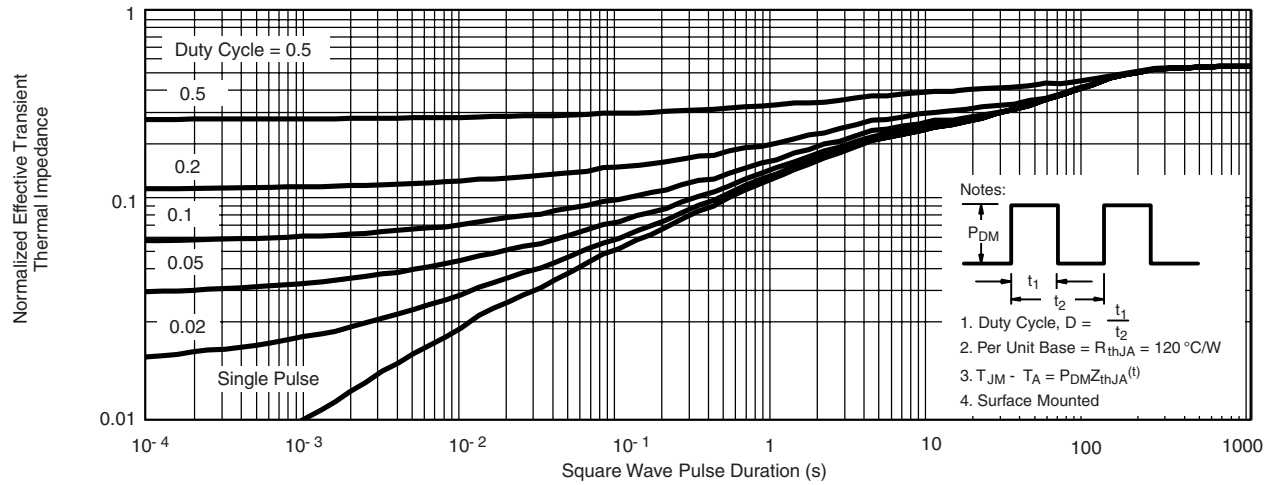
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

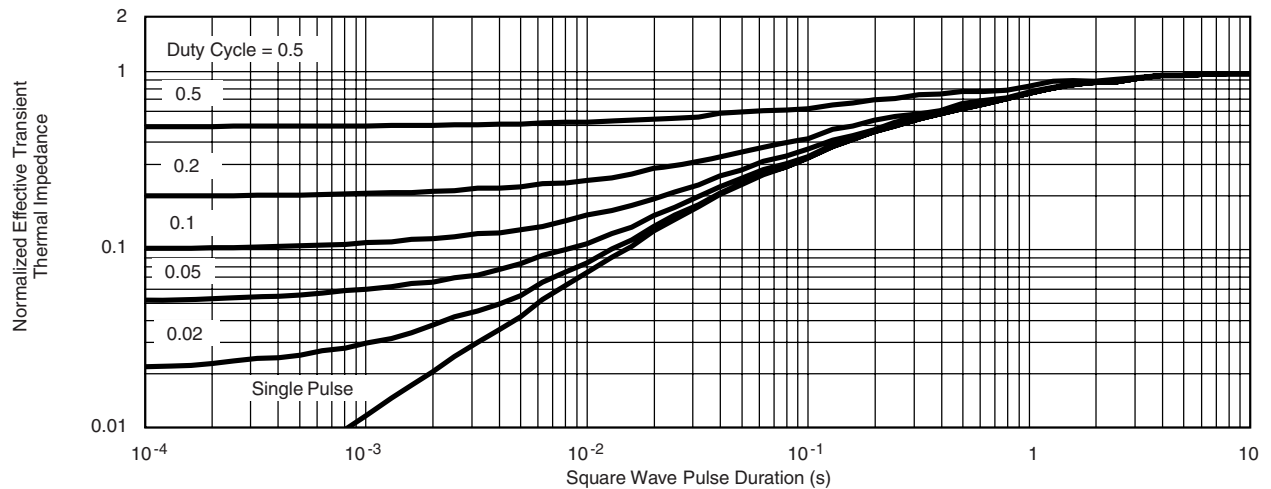
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Current Derating*****Power Derating, Junction-to-Foot****Power Derating, Junction-to-Ambient**

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

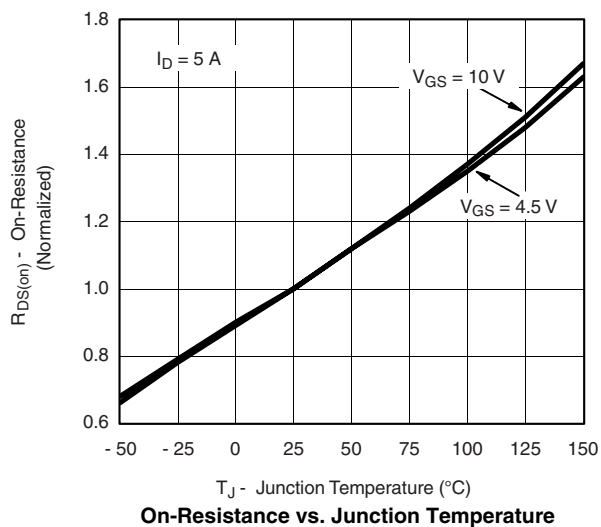
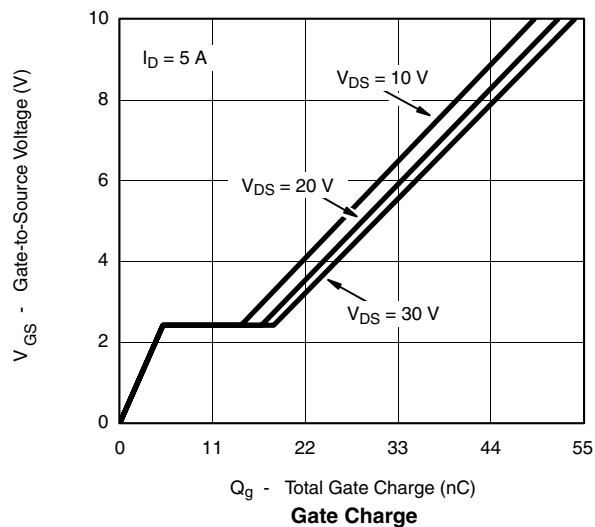
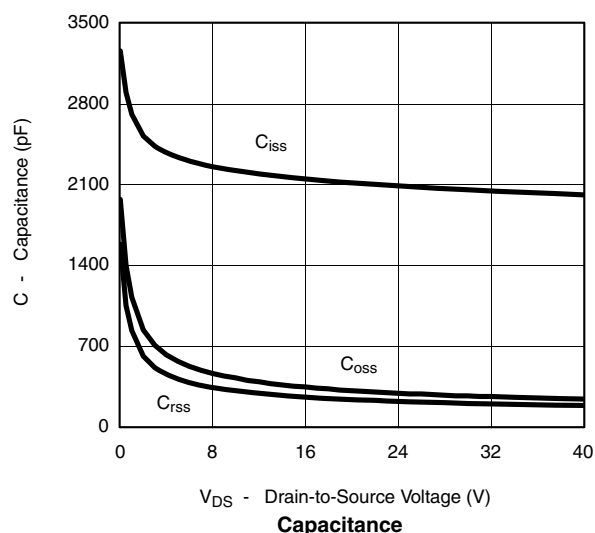
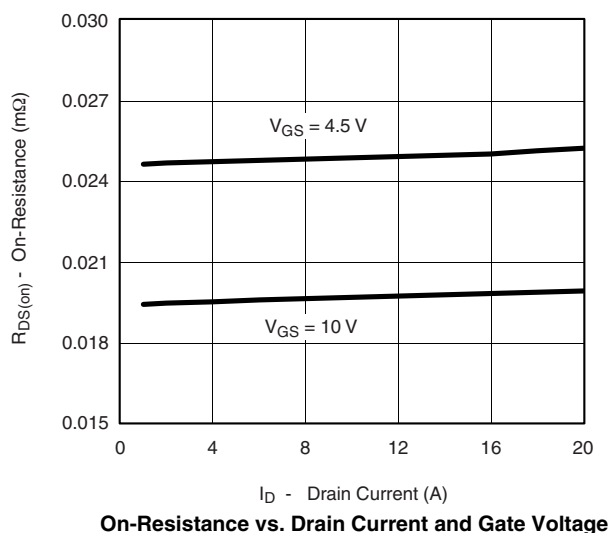
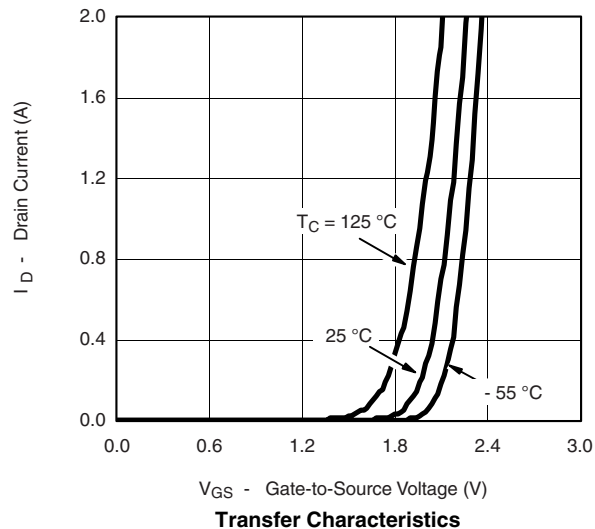
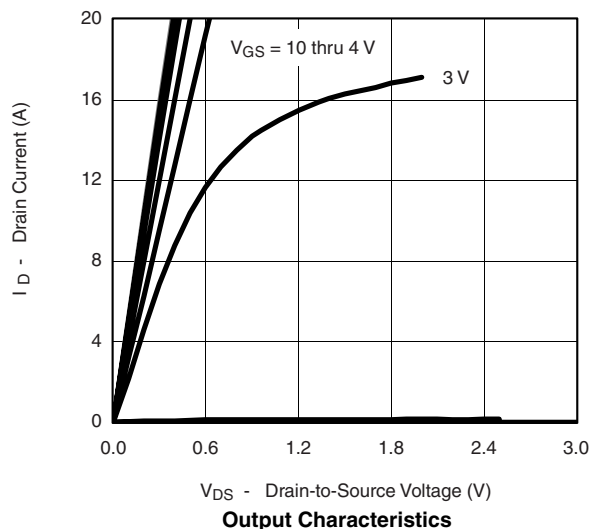
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



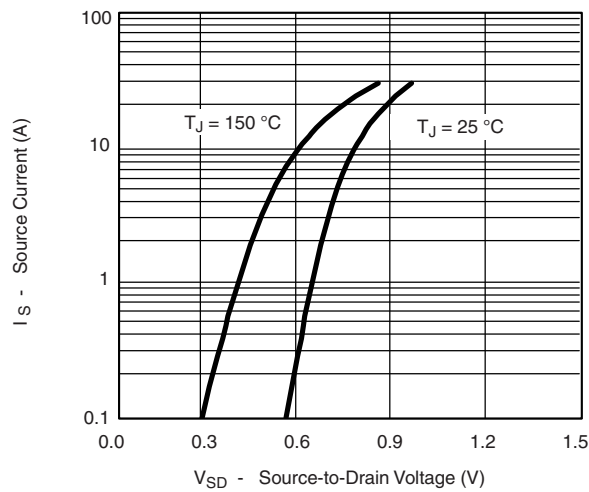
Normalized Thermal Transient Impedance, Junction-to-Ambient



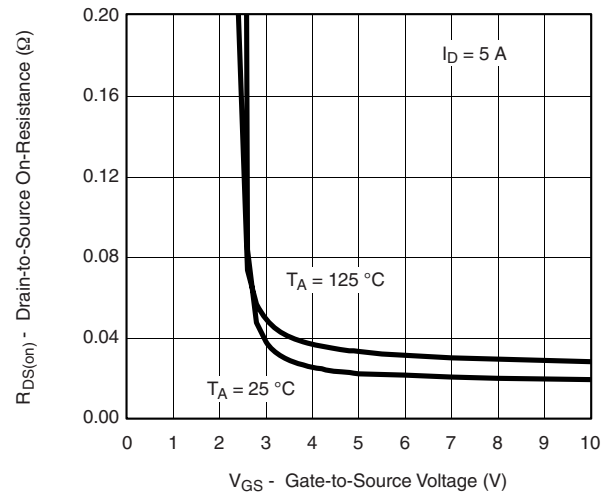
Normalized Thermal Transient Impedance, Junction-to-Case

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

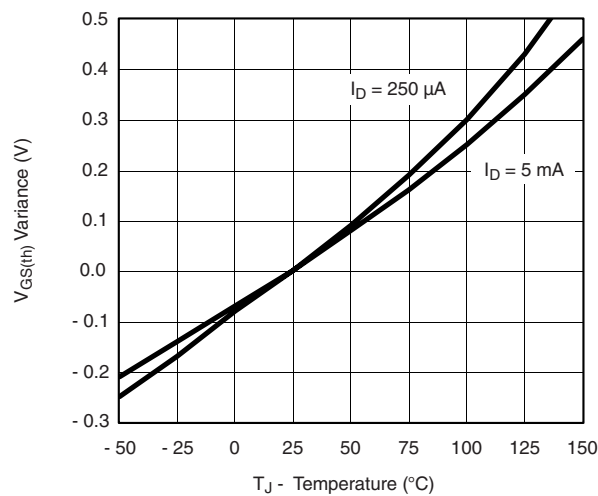
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



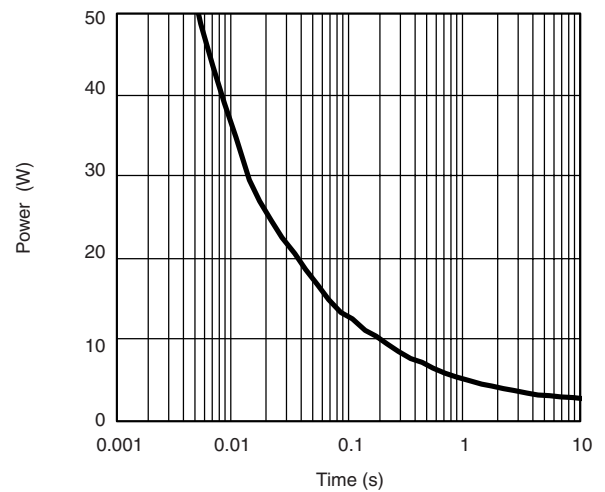
Source-Drain Diode Forward Voltage



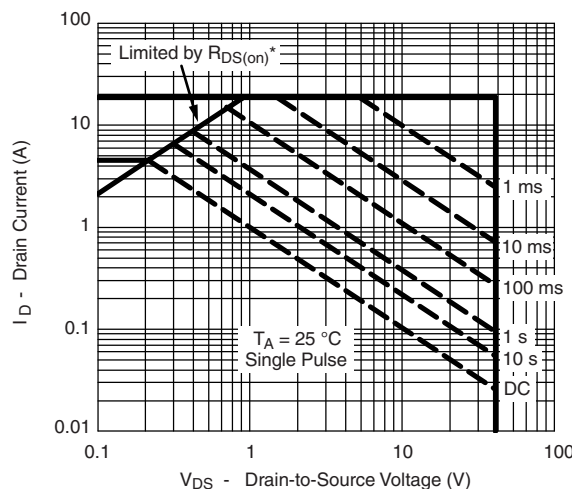
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

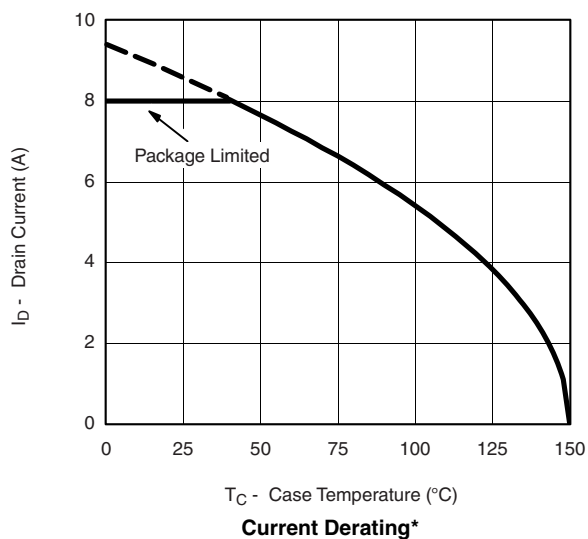
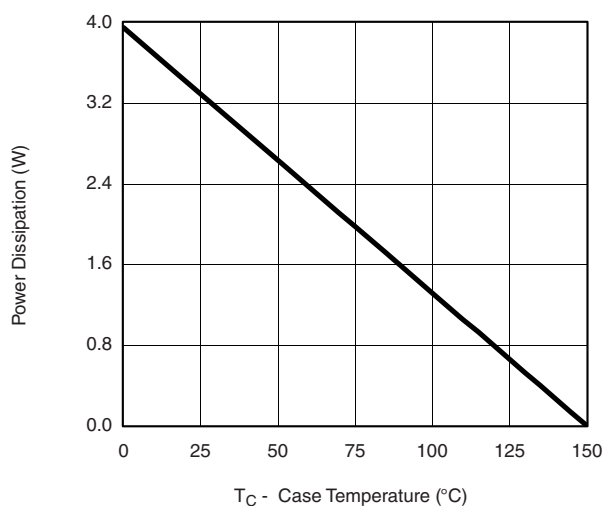
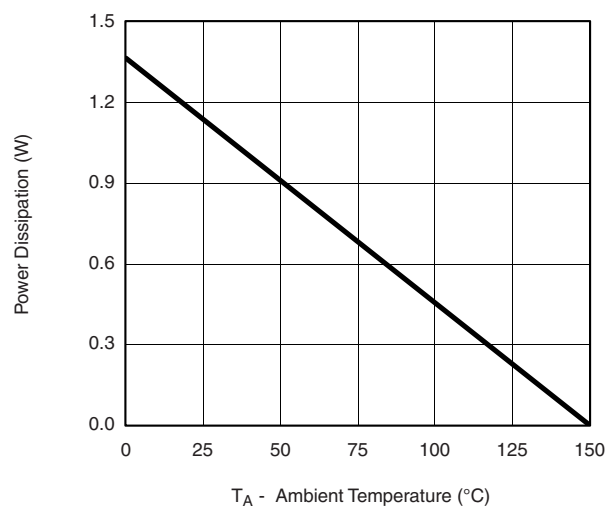


Single Pulse Power, Junction-to-Ambient



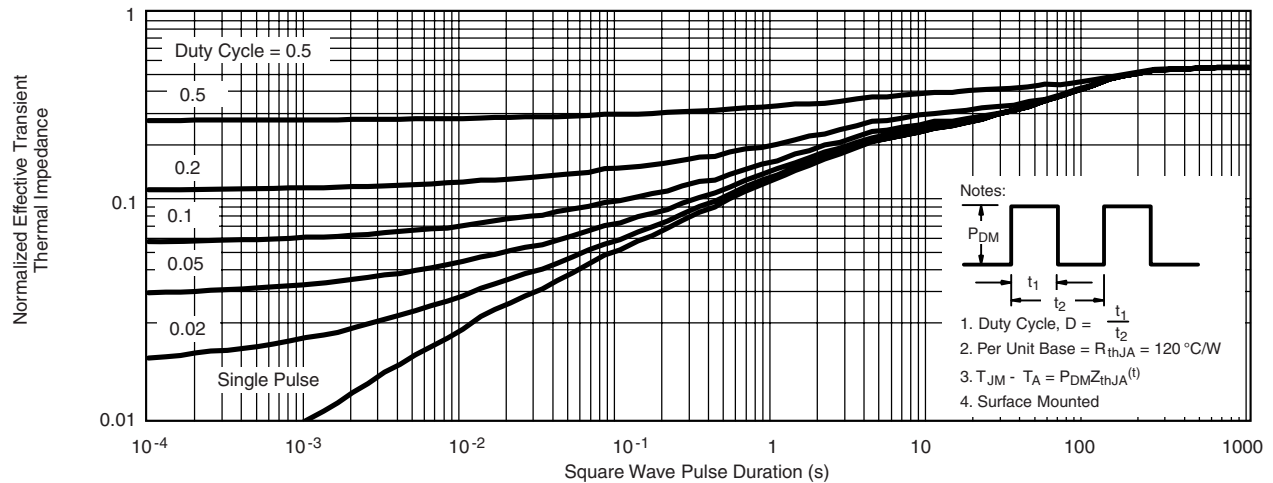
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

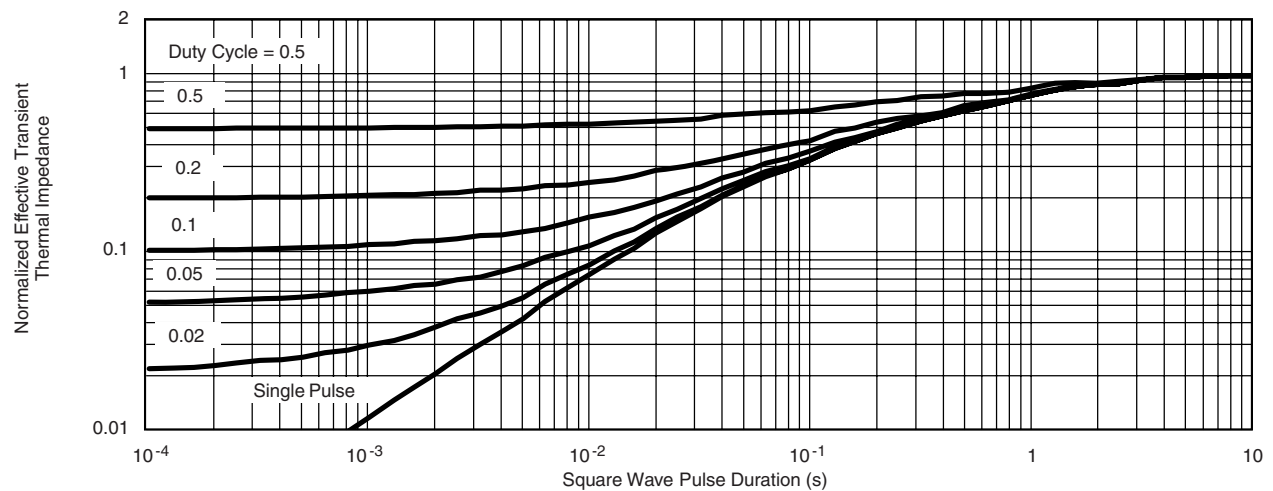
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Current Derating*****Power Derating, Junction-to-Foot****Power Derating, Junction-to-Ambient**

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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